

### Features

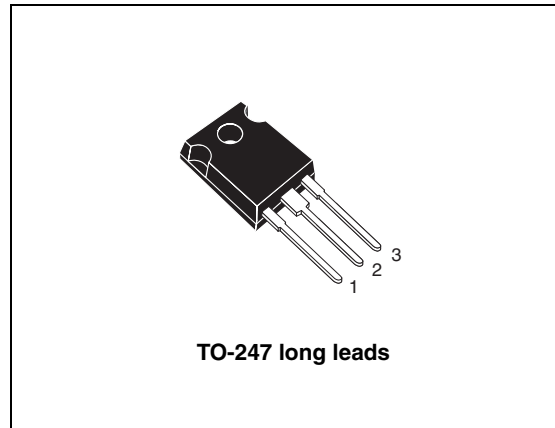
- Low  $C_{RES} / C_{IES}$  ratio (no cross conduction susceptibility)
- IGBT co-packaged with ultra fast free-wheeling diode

### Applications

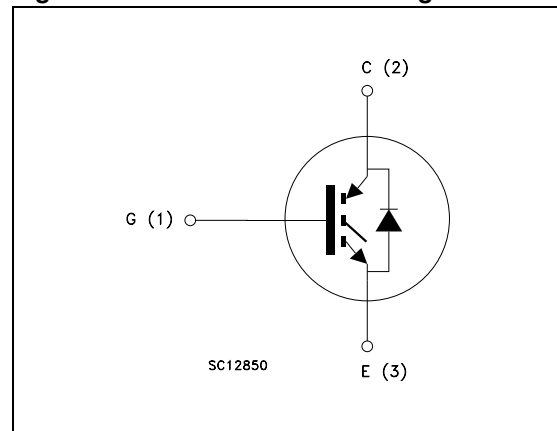
- High frequency inverters
- UPS
- Motor drivers
- Induction heating

### Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order code	Marking	Package	Packaging
STGW45NC60VD	GW45NC60VD	TO-247 long leads	Tube

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# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	7
	2.2 Frequency applications .....	9
<b>3</b>	<b>Test circuit</b> .....	<b>11</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>12</b>
<b>5</b>	<b>Revision history</b> .....	<b>14</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	600	V
$I_C^{(1)}$	Collector current (continuous) at 25 °C	90	A
$I_C^{(1)}$	Collector current (continuous) at 100 °C	50	A
$I_{CL}^{(2)}$	Turn-off latching current	220	A
$I_{CP}^{(3)}$	Pulsed collector current	220	A
$V_{GE}$	Gate-emitter voltage	± 20	V
$I_F$	Diode RMS forward current at $T_C = 25$ °C	30	A
$I_{FSM}$	Surge non repetitive forward current ( $t_p=10$ ms sinusoidal)	120	A
$P_{TOT}$	Total dissipation at $T_C = 25$ °C	270	W
$T_j$	Operating junction temperature	– 55 to 150	°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C) \cdot I_C}$$

2.  $V_{clamp} = 80\%(V_{CES})$ ,  $T_j = 150$  °C,  $R_G = 10$  Ω,  $V_{GE} = 15$  V

3. Pulse width limited by max. junction temperature allowed

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (IGBT) max	0.46	°C/W
$R_{thj-case}$	Thermal resistance junction-case (diode) max	1.5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	°C/W

## 2 Electrical characteristics

( $T_{CASE}=25\text{ °C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ( $V_{GE} = 0$ )	$I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_C = 125\text{ °C}$		1.8 1.7	2.4	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	3.75		5.75	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 600\text{ V}$ $V_{CE} = 600\text{ V}, T_C = 125\text{ °C}$			500 5	$\mu\text{A}$ mA
$I_{GES}$	Gate-emitter leakage current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20\text{ V}$			$\pm 100$	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 15\text{ V}, I_C = 30\text{ A}$		20		S

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0$		290		pF
$C_{oes}$	Output capacitance			0		pF
$C_{res}$	Reverse transfer capacitance			298		pF
$Q_g$	Total gate charge	$V_{CE} = 390\text{ V}, I_C = 30\text{ A},$ $V_{GE} = 15\text{ V}$ <i>(see Figure 19)</i>		126		nC
$Q_{ge}$	Gate-emitter charge			16		nC
$Q_{gc}$	Gate-collector charge			46		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390 \text{ V}$ , $I_C = 30 \text{ A}$ ,		33		ns
$t_r$	Current rise time	$R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$		13		ns
$(di/dt)_{onf}$	Turn-on current slope	(see Figure 18)		2500		A/ $\mu$ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390 \text{ V}$ , $I_C = 30 \text{ A}$ ,		32		ns
$t_r$	Current rise time	$R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$		14		ns
$(di/dt)_{on}$	Turn-on current slope	$T_C = 125 \text{ }^\circ\text{C}$ (see Figure 18)		2280		A/ $\mu$ s
$t_{r(Voff)}$	Off voltage rise time	$V_{CC} = 390 \text{ V}$ , $I_C = 30 \text{ A}$ ,		33		ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$		178		ns
$t_f$	Current fall time	(see Figure 18)		65		ns
$t_{r(Voff)}$	Off voltage rise time	$V_{CC} = 390 \text{ V}$ , $I_C = 30 \text{ A}$ ,		68		ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$		238		ns
$t_f$	Current fall time	$T_C = 125 \text{ }^\circ\text{C}$ (see Figure 18)		128		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 390 \text{ V}$ , $I_C = 30 \text{ A}$		333		$\mu$ J
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ ,		537		$\mu$ J
$E_{ts}$	Total switching losses	(see Figure 20)		870		$\mu$ J
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 390 \text{ V}$ , $I_C = 30 \text{ A}$		618		$\mu$ J
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ ,		1125		$\mu$ J
$E_{ts}$	Total switching losses	$T_C = 125 \text{ }^\circ\text{C}$ (see Figure 20)		1743		$\mu$ J

1.  $E_{on}$  is the turn-on losses when a typical diode is used in the test circuit in figure 2  $E_{on}$  include diode recovery energy. If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs and diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward on-voltage	$I_F = 30\text{ A}$ $I_F = 30\text{ A}, T_C = 125\text{ °C}$		2.4		V
				1.8		V
$t_{rr}$	Reverse recovery time	$I_F = 30\text{ A}, V_R = 50\text{ V},$ $di/dt = 100\text{ A}/\mu\text{s}$ <i>(see Figure 21)</i>		45		ns
$Q_{rr}$	Reverse recovery charge			56		nC
$I_{rrm}$	Reverse recovery current			2.55		A
$t_{rr}$	Reverse recovery time	$I_F = 30\text{ A}, V_R = 50\text{ V},$ $T_C = 125\text{ °C},$ $di/dt = 100\text{ A}/\mu\text{s}$ <i>(see Figure 21)</i>		100		ns
$Q_{rr}$	Reverse recovery charge			290		nC
$I_{rrm}$	Reverse recovery current			5.8		A

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

Figure 3. Transfer characteristics

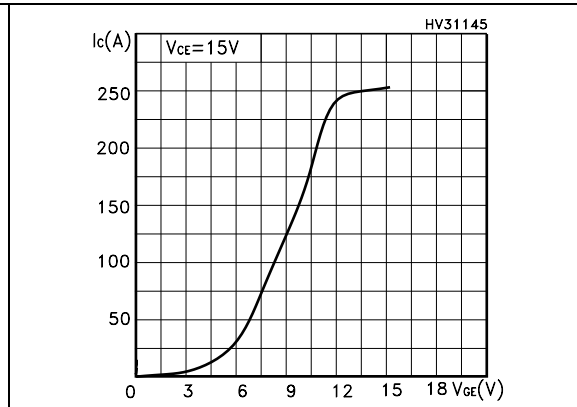
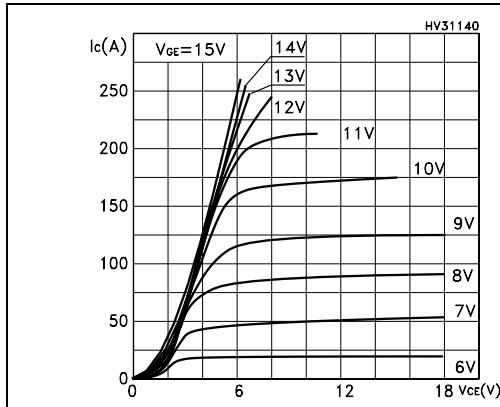


Figure 4. Transconductance

Figure 5. Collector-emitter on voltage vs temperature

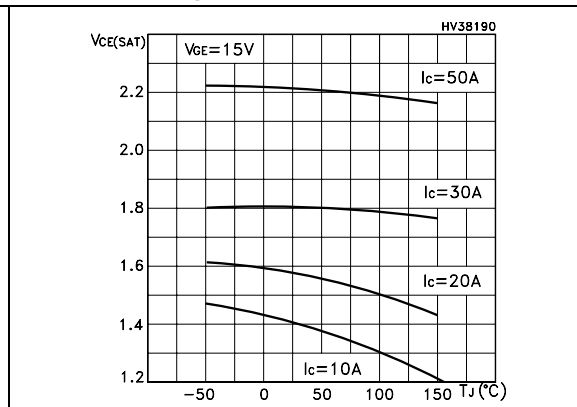
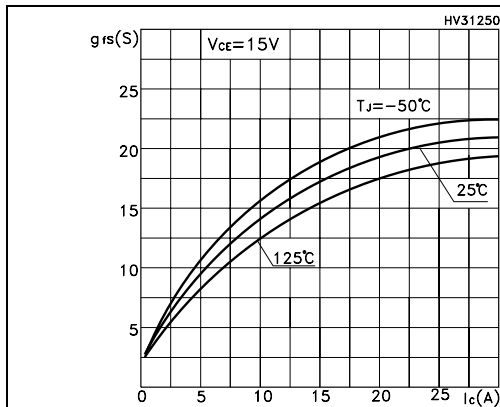


Figure 6. Collector-emitter on voltage vs collector current

Figure 7. Normalized gate threshold vs temperature

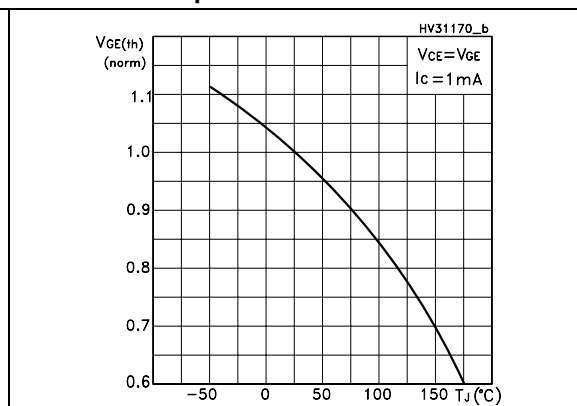
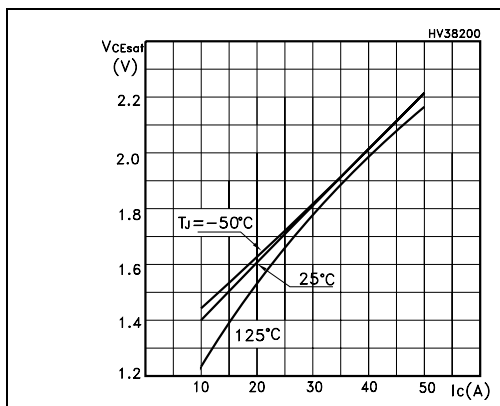


Figure 8. Normalized breakdown voltage vs temperature

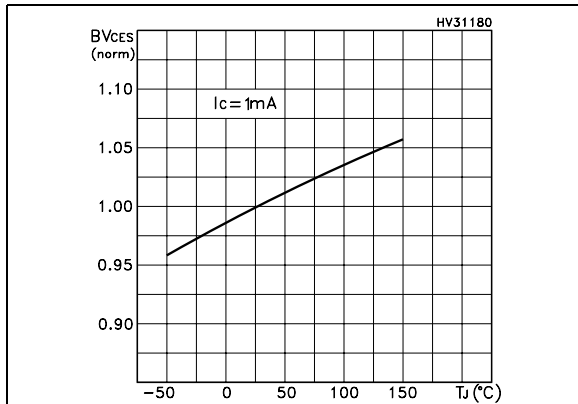


Figure 9. Gate charge vs gate-emitter voltage

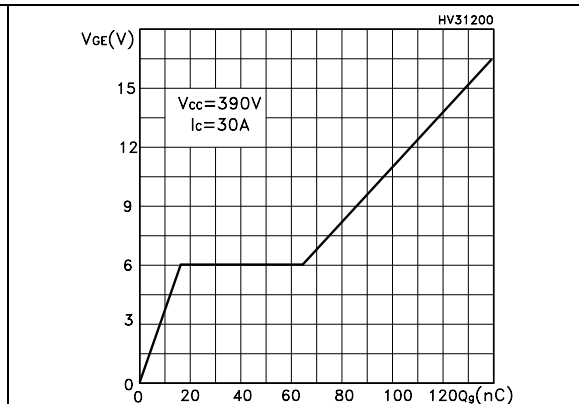


Figure 10. Capacitance variations

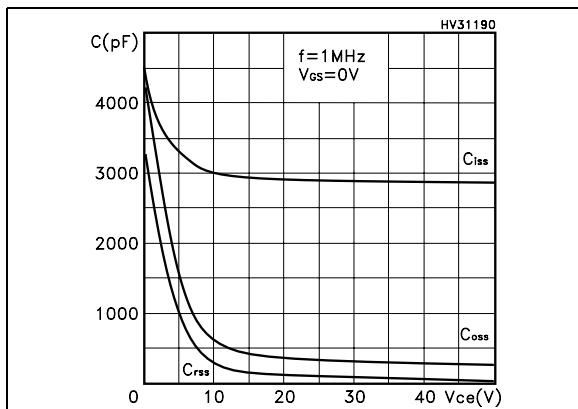


Figure 11. Switching losses vs temperature

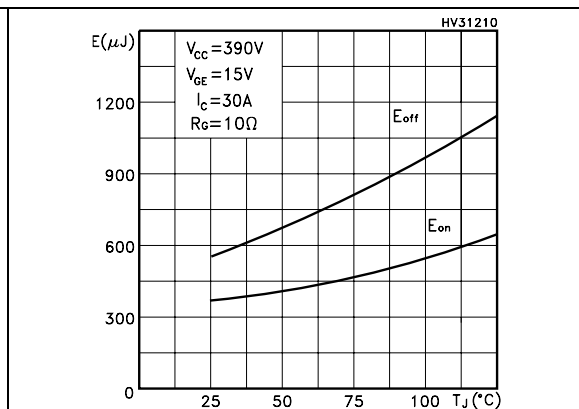


Figure 12. Switching losses vs gate resistance Figure 13. Switching losses vs collector current

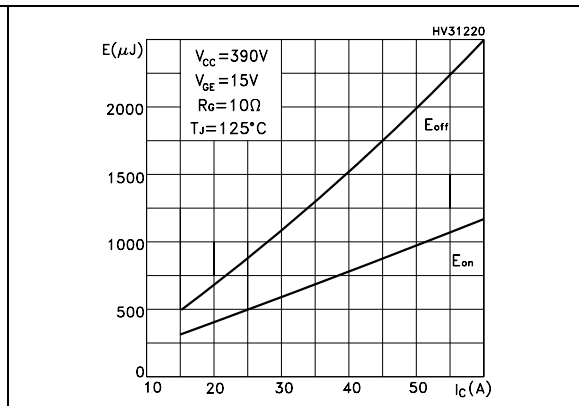
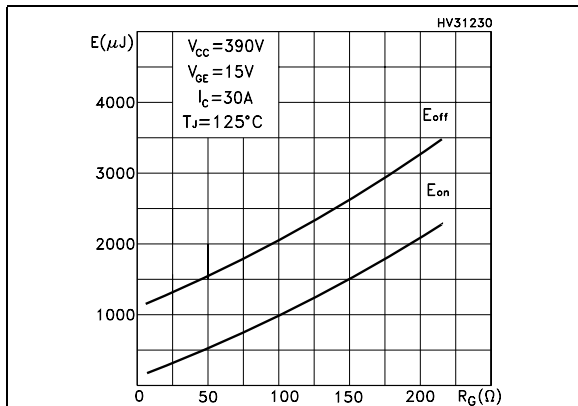




Figure 14. Thermal impedance

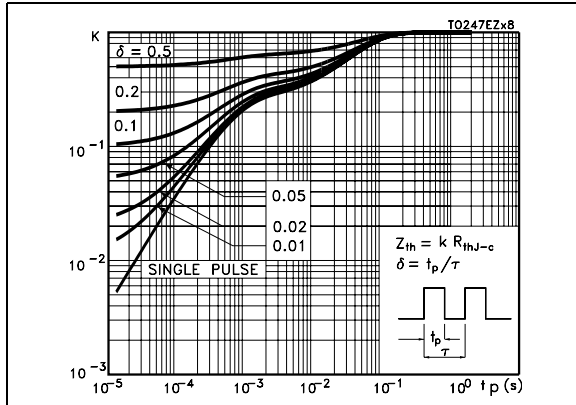


Figure 15. Turn-off SOA

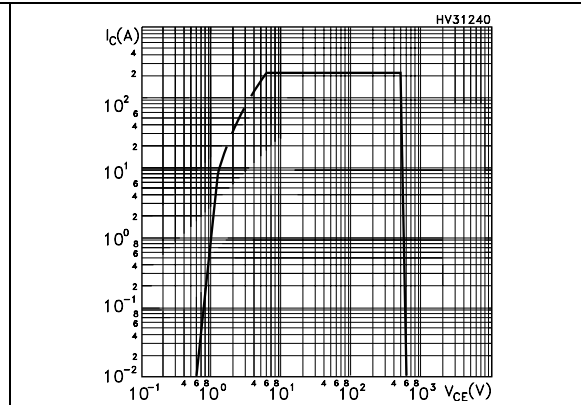


Figure 16. Emitter-collector diode characteristics

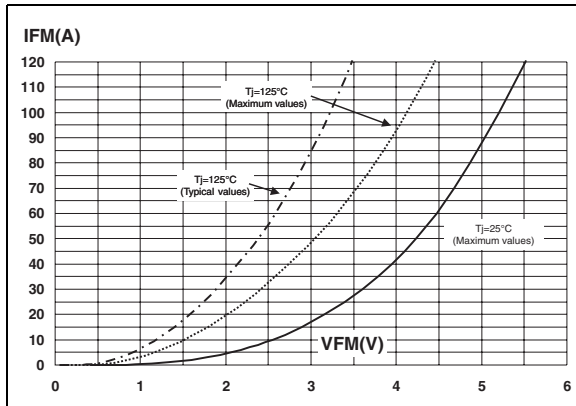
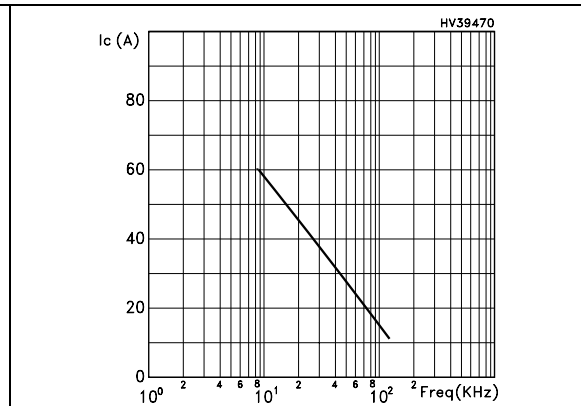


Figure 17. Ic vs. frequency



## 2.2 Frequency applications

For a fast IGBT suitable for high frequency applications, the typical collector current vs. maximum operating frequency curve is reported. That frequency is defined as follows:

$$f_{MAX} = (P_D - P_C) / (E_{ON} + E_{OFF})$$

- The maximum power dissipation is limited by maximum junction to case thermal resistance:

### Equation 1

$$P_D = \Delta T / R_{THJ-C}$$

considering  $\Delta T = T_J - T_C = 125 \text{ }^\circ\text{C} - 75 \text{ }^\circ\text{C} = 50 \text{ }^\circ\text{C}$

- The conduction losses are:

**Equation 2**

$$P_C = I_C * V_{CE(SAT)} * \delta$$

with 50% of duty cycle,  $V_{CESAT}$  typical value @ 125 °C.

- Power dissipation during ON and OFF commutations is due to the switching frequency:

**Equation 3**

$P_{SW} = (E_{ON} + E_{OFF}) * \text{freq.}$  Typical values @ 125 °C for switching losses are used (test conditions:  $V_{CE} = 390 \text{ V}$ ,  $V_{GE} = 15 \text{ V}$ ,  $R_G = 10 \Omega$ ). Furthermore, diode recovery energy is included in the  $E_{ON}$  (see note 2), while the tail of the collector current is included in the  $E_{OFF}$  measurements (see note 3).

### 3 Test circuit

Figure 18. Test circuit for inductive load switching

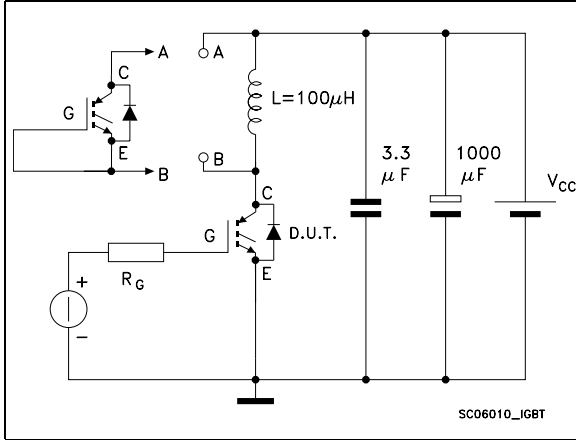


Figure 19. Gate charge test circuit

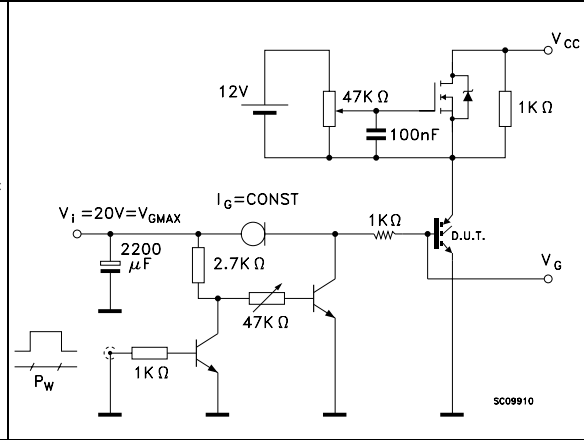


Figure 20. Switching waveforms

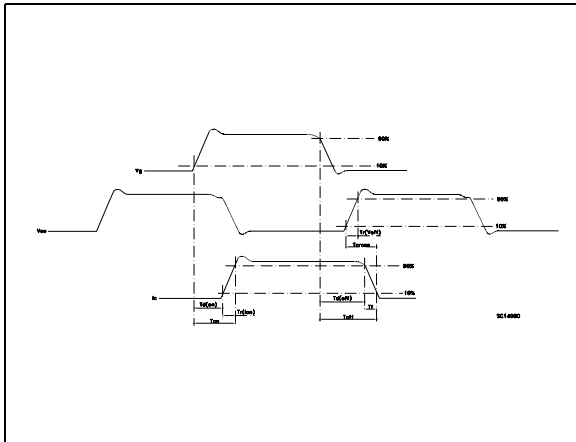
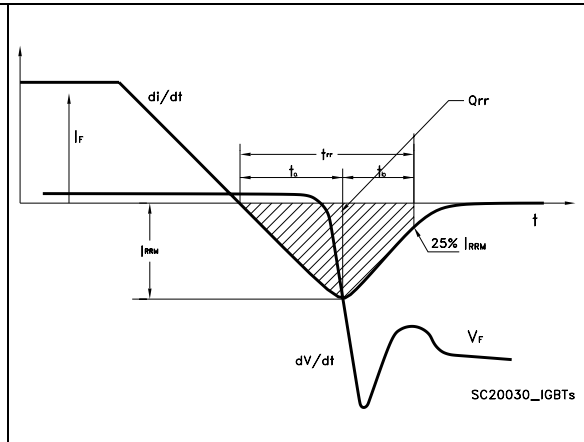


Figure 21. Diode recovery times waveform

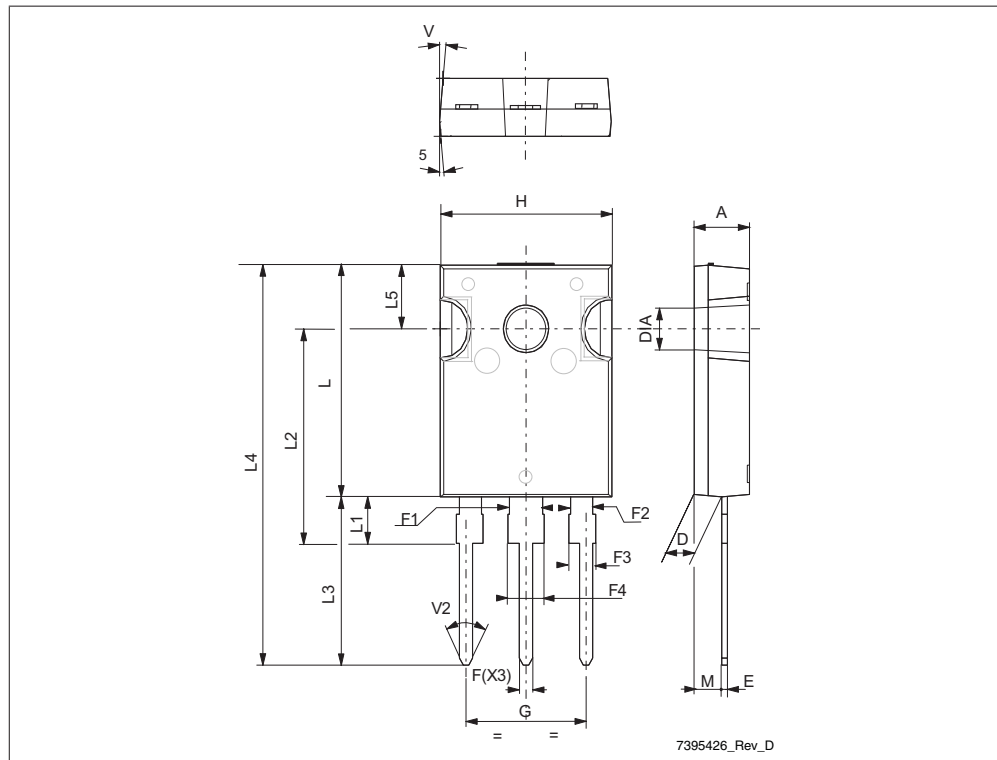


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.16
D	2.2		2.6
E	0.4		0.8
F	1		1.4
F1		3	
F2		2	
F3	1.9		2.4
F4	3		3.4
G		10.9	
H	15.45		16.03
L	19.85		21.09
L1	3.7		4.3
L2	18.3		19.13
L3	14.2		20.3
L4	34.05		41.38
L5	5.35		6.3
M	2		3
V		5°	
V2		60°	
DIA	3.55		3.65



## 5 Revision history

Table 9. Document revision history

Date	Revision	Changes
19-Mar-2008	1	First release

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